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STPS41L45CG/CT/CR

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 20 A
V_{RRM}	45 V
T_j (max)	150 °C
V_F (max)	0.47 V

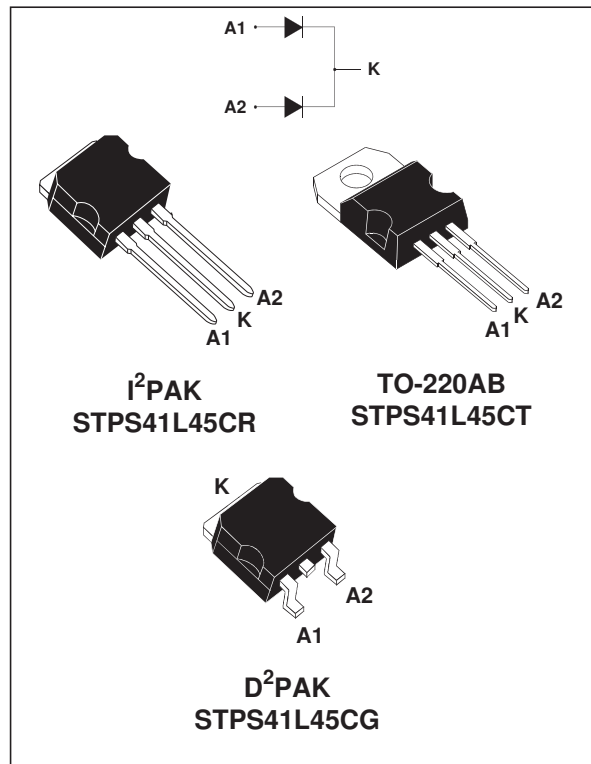
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tab Schottky rectifier suited for 5V output in off line AC/DC power supplies.

Packaged in D²PAK, I²PAK and TO-220AB this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		45	V
$I_{F(RMS)}$	RMS forward current		30	A
$I_{F(AV)}$	Average forward current	$T_c = 130^\circ\text{C}$ $\delta = 0.5$	Per diode: 20 Per device: 40	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10$ ms sinusoidal	220	A
I_{RRM}	Peak repetitive reverse current	$t_p = 2$ μs square $F = 1$ kHz	1	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1$ μs $T_j = 25^\circ\text{C}$	10000	W
T_{stg}	Storage temperature range		- 65 to + 175	°C
T_j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS41L45CG / STPS41L45CT / STPS41L45CR

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.5	$^{\circ}\text{C/W}$
		Total	0.8	
$R_{th(c)}$	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			1.2	mA
		$T_j = 125^{\circ}\text{C}$			110	220	mA
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 20\text{ A}$			0.53	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 20\text{ A}$		0.42	0.47	
		$T_j = 25^{\circ}\text{C}$	$I_F = 40\text{ A}$			0.68	
		$T_j = 125^{\circ}\text{C}$	$I_F = 40\text{ A}$		0.60	0.66	

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.28 \times I_{F(AV)} + 0.0095 I_{F(RMS)}^2$$

Fig. 1: Conduction losses versus average current.

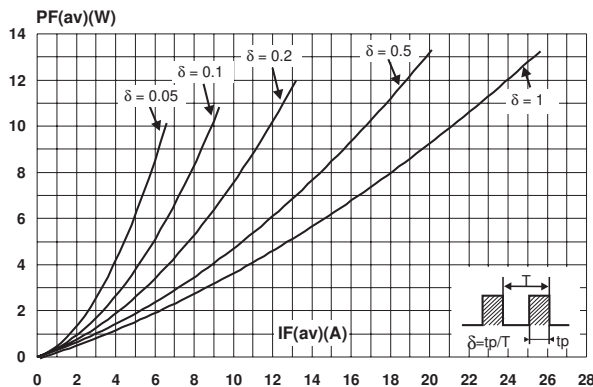


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

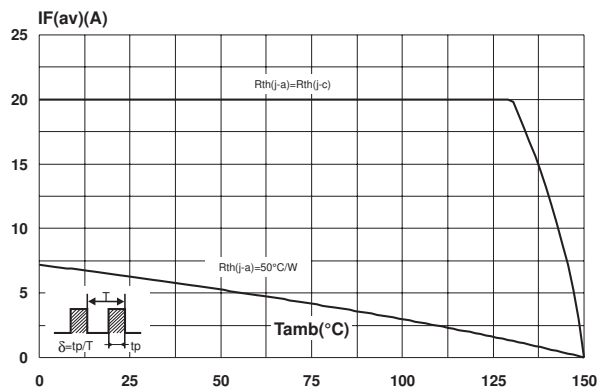


Fig. 3: Normalized avalanche power derating versus pulse duration.

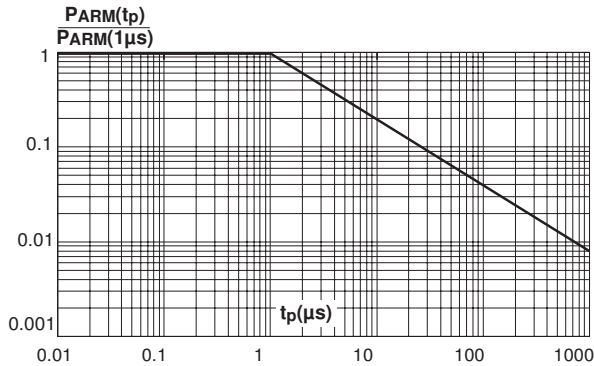


Fig. 4: Normalized avalanche power derating versus junction temperature.

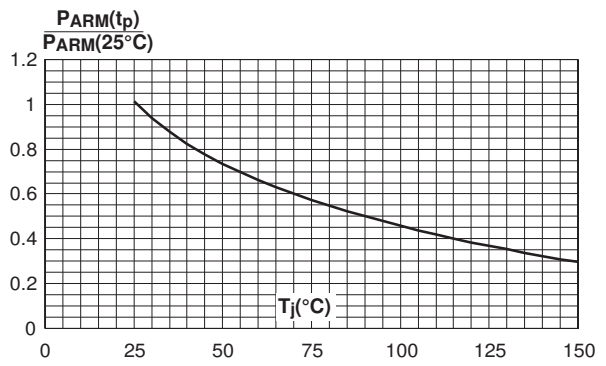


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

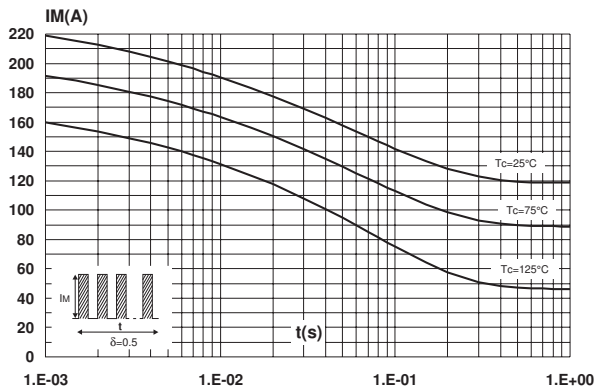


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

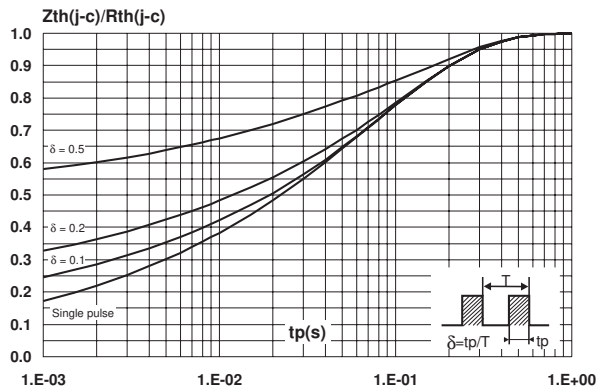


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

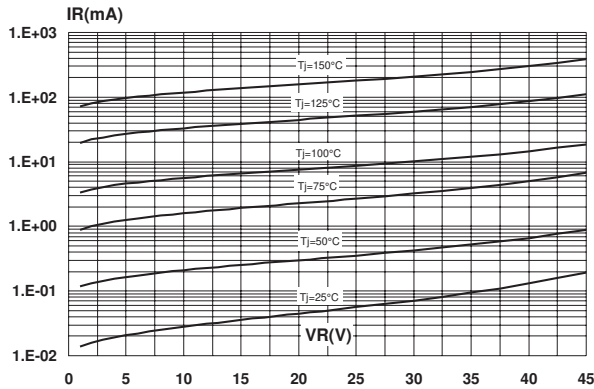
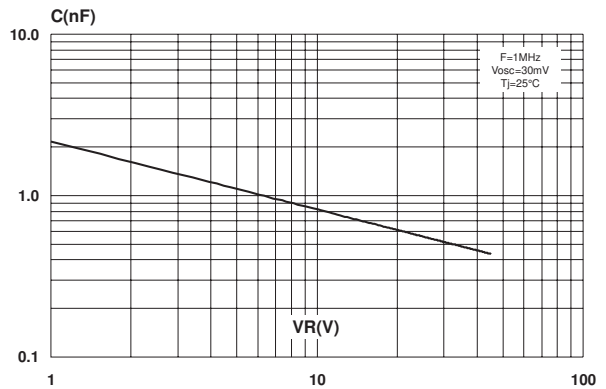


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).



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Fig. 9: Forward voltage drop versus forward current.

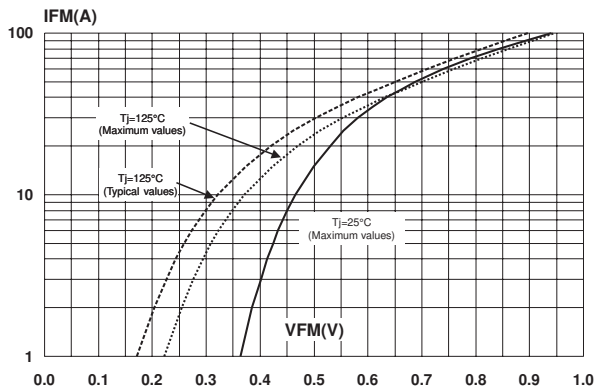
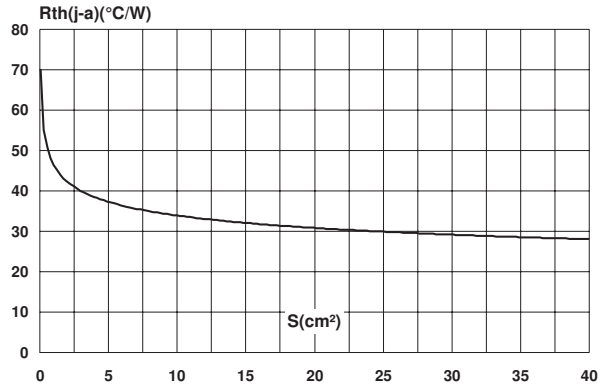


Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35µm) (STPS41L45CG only).

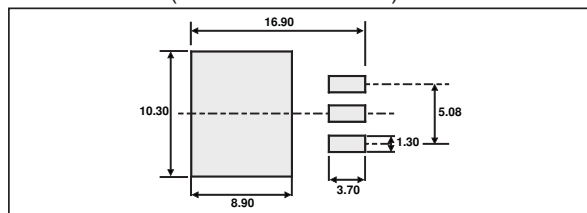


PACKAGE MECHANICAL DATA
D²PAK

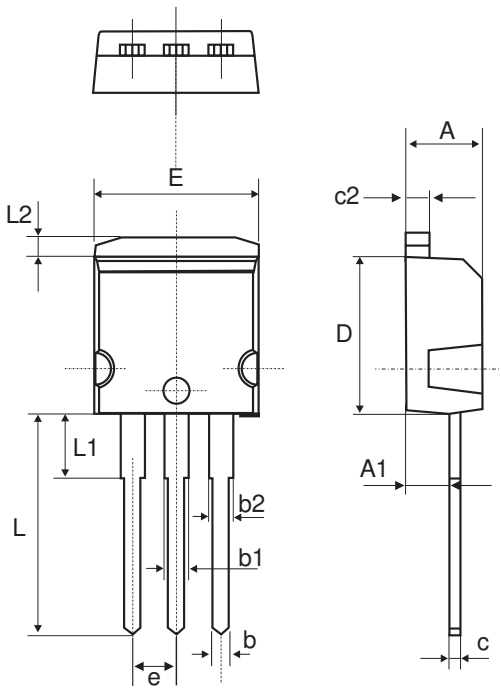
* FLAT ZONE NO LESS THAN 2mm

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

FOOTPRINT (dimensions in mm)



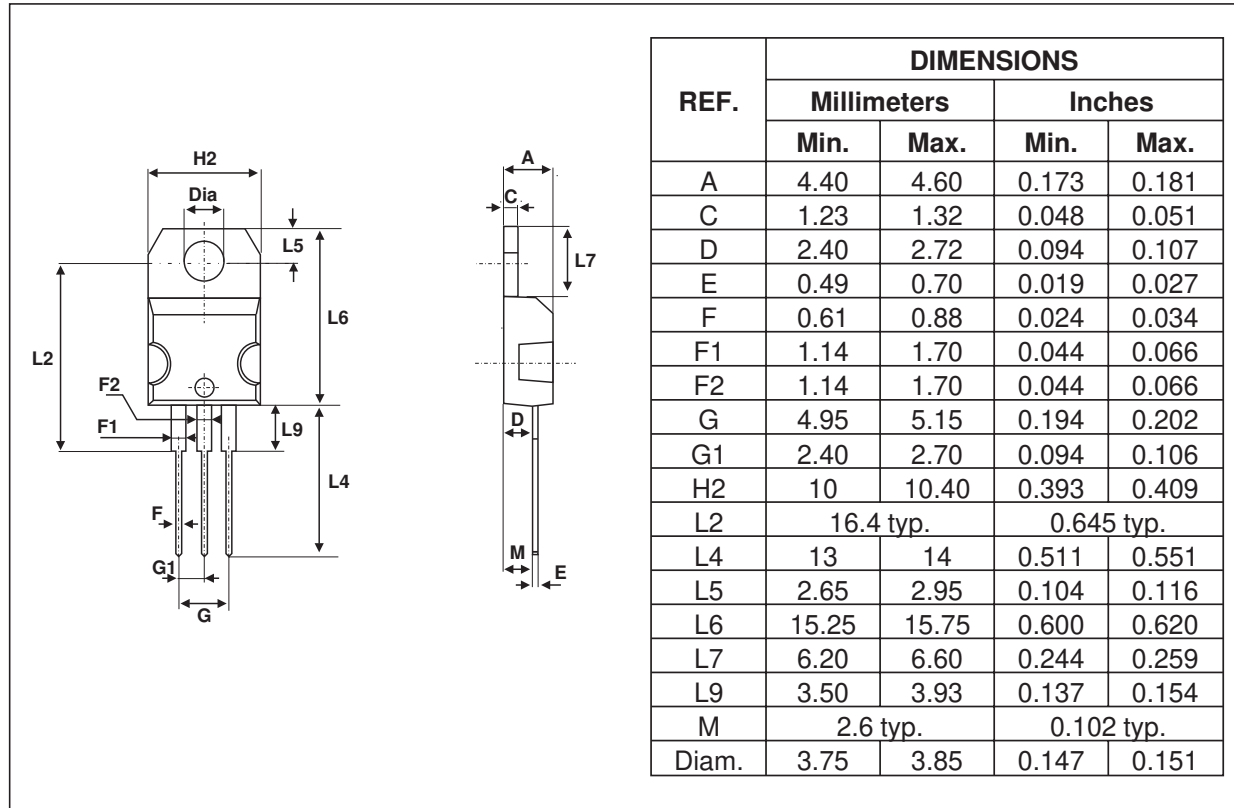
PACKAGE MECHANICAL DATA
I²PAK



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
b	0.70	0.93	0.028	0.037
b1	1.14	1.17	0.044	0.046
b2	1.14	1.17	0.044	0.046
c	0.45	0.60	0.018	0.024
c2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
E	10.0	10.4	0.394	0.409
L	13.1	13.6	0.516	0.535
L1	3.48	3.78	0.137	0.149
L2	1.27	1.40	0.050	0.055

STPS41L45CG / STPS41L45CT / STPS41L45CR

PACKAGE MECHANICAL DATA
TO-220AB



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS41L45CG	STPS41L45CG	D ² PAK	1.48 g	50	Tube
STPS41L45CG-TR	STPS41L45CG	D ² PAK	1.48 g	1000	Tape & reel
STPS41L45CT	STPS41L45CT	TO-220AB	2.20 g	50	Tube
STPS41L45CR	STPS41L45CR	I ² PAK	1.49 g	50	Tube

■ EPOXY MEETS UL94,V0

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